

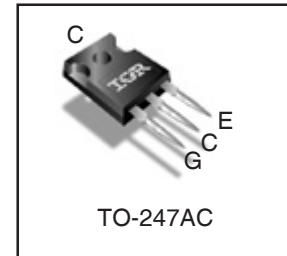
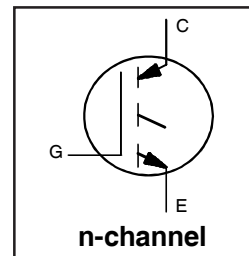
IRGP4065PbF

PDP TRENCH IGBT

Features

- Advanced Trench IGBT Technology
- Optimized for Sustain and Energy Recovery circuits in PDP applications
- Low $V_{CE(on)}$ and Energy per Pulse (E_{PULSE}^{TM}) for improved panel efficiency
- High repetitive peak current capability
- Lead Free package

| Key Parameters | | |
|--------------------------------------|------|------------|
| $V_{CE\ min}$ | 300 | V |
| $V_{CE(on)}\ typ.\ @\ I_C = 70A$ | 1.75 | V |
| $I_{RP}\ max\ @\ T_C = 25^\circ C$ ① | 205 | A |
| $T_J\ max$ | 150 | $^\circ C$ |



| G | C | E |
|------|-----------|---------|
| Gate | Collector | Emitter |

Description

This IGBT is specifically designed for applications in Plasma Display Panels. This device utilizes advanced trench IGBT technology to achieve low $V_{CE(on)}$ and low E_{PULSE}^{TM} rating per silicon area which improve panel efficiency. Additional features are $150^\circ C$ operating junction temperature and high repetitive peak current capability. These features combine to make this IGBT a highly efficient, robust and reliable device for PDP applications.

Absolute Maximum Ratings

| | Parameter | Max. | Units |
|-----------------------------|---|------------------|--------------|
| V_{GE} | Gate-to-Emitter Voltage | ± 30 | V |
| $I_C @ T_C = 25^\circ C$ | Continuous Collector Current, $V_{GE} @ 15V$ | 70 | A |
| $I_C @ T_C = 100^\circ C$ | Continuous Collector, $V_{GE} @ 15V$ | 40 | |
| $I_{RP} @ T_C = 25^\circ C$ | Repetitive Peak Current ① | 205 | |
| $P_D @ T_C = 25^\circ C$ | Power Dissipation | 178 | W |
| $P_D @ T_C = 100^\circ C$ | Power Dissipation | 71 | |
| | Linear Derating Factor | 1.4 | $W/^\circ C$ |
| T_J T_{STG} | Operating Junction and Storage Temperature Range | -40 to + 150 | $^\circ C$ |
| | Soldering Temperature for 10 seconds | 300 | |
| | Mounting Torque, 6-32 or M3 Screw | 10lb·in (1.1N·m) | |

Thermal Resistance

| | Parameter | Typ. | Max. | Units |
|-----------------|--|------|------|--------------|
| $R_{\theta JC}$ | Junction-to-Case ② | — | 0.80 | $^\circ C/W$ |
| $R_{\theta CS}$ | Case-to-Sink (flat, greased surface) | 0.24 | — | |
| $R_{\theta JA}$ | Junction-to-Ambient (typical socket mount) | — | 40 | |

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

| | Parameter | Min. | Typ. | Max. | Units | Conditions |
|--------------------------------|--|------|------|------|----------------------|--|
| BV_{CES} | Collector-to-Emitter Breakdown Voltage | 300 | — | — | V | $V_{GE} = 0V, I_{CE} = 1\text{ mA}$ |
| $\Delta BV_{CES}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient | — | 0.23 | — | V/ $^\circ\text{C}$ | Reference to 25°C , $I_{CE} = 1\text{ mA}$ |
| $V_{CE(on)}$ | Static Collector-to-Emitter Voltage | — | 1.20 | 1.40 | V | $V_{GE} = 15V, I_{CE} = 25A$ ③ |
| | | — | 1.35 | — | | $V_{GE} = 15V, I_{CE} = 40A$ ③ |
| | | — | 1.75 | 2.10 | | $V_{GE} = 15V, I_{CE} = 70A$ ③ |
| | | — | 2.35 | — | | $V_{GE} = 15V, I_{CE} = 120A$ ③ |
| | | — | 2.00 | — | | $V_{GE} = 15V, I_{CE} = 70A, T_J = 150^\circ\text{C}$ |
| $V_{GE(th)}$ | Gate Threshold Voltage | 2.6 | — | 5.0 | V | $V_{CE} = V_{GE}, I_{CE} = 500\mu\text{A}$ |
| $\Delta V_{GE(th)}/\Delta T_J$ | Gate Threshold Voltage Coefficient | — | -11 | — | mV/ $^\circ\text{C}$ | |
| I_{CES} | Collector-to-Emitter Leakage Current | — | 2.0 | 25 | μA | $V_{CE} = 300V, V_{GE} = 0V$ |
| | | — | 50 | — | | $V_{CE} = 300V, V_{GE} = 0V, T_J = 150^\circ\text{C}$ |
| I_{GES} | Gate-to-Emitter Forward Leakage | — | — | 100 | nA | $V_{GE} = 30V$ |
| | Gate-to-Emitter Reverse Leakage | — | — | -100 | | $V_{GE} = -30V$ |
| g_{fe} | Forward Transconductance | — | 26 | — | S | $V_{CE} = 25V, I_{CE} = 25A$ |
| Q_g | Total Gate Charge | — | 62 | — | nC | $V_{CE} = 200V, I_C = 25A, V_{GE} = 15V$ ③ |
| Q_{gc} | Gate-to-Collector Charge | — | 20 | — | | |
| t_{st} | Shoot Through Blocking Time | 100 | — | — | ns | $V_{CC} = 240V, V_{GE} = 15V, R_G = 5.1\Omega$ |
| E_{PULSE} | Energy per Pulse | — | 875 | — | μJ | $L = 220\text{nH}, C = 0.40\mu\text{F}, V_{GE} = 15V$ $V_{CC} = 240V, R_G = 5.1\Omega, T_J = 25^\circ\text{C}$ |
| | | — | 975 | — | | $L = 220\text{nH}, C = 0.40\mu\text{F}, V_{GE} = 15V$ $V_{CC} = 240V, R_G = 5.1\Omega, T_J = 100^\circ\text{C}$ |
| C_{iss} | Input Capacitance | — | 2200 | — | pF | $V_{GE} = 0V$ |
| C_{oss} | Output Capacitance | — | 110 | — | | $V_{CE} = 30V$ |
| C_{rss} | Reverse Transfer Capacitance | — | 55 | — | | $f = 1.0\text{MHz}$, See Fig.13 |
| L_C | Internal Collector Inductance | — | 5.0 | — | nH | Between lead, 6mm (0.25in.) |
| L_E | Internal Emitter Inductance | — | 13 | — | | from package and center of die contact |

Notes:

- ① Half sine wave with duty cycle = 0.25, $t_{on} = 1\mu\text{sec}$.
- ② R_θ is measured at T_J of approximately 90°C .
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.

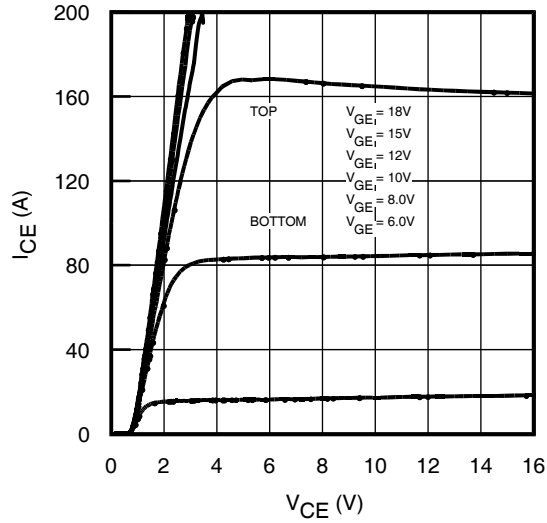


Fig 1. Typical Output Characteristics @ 25°C

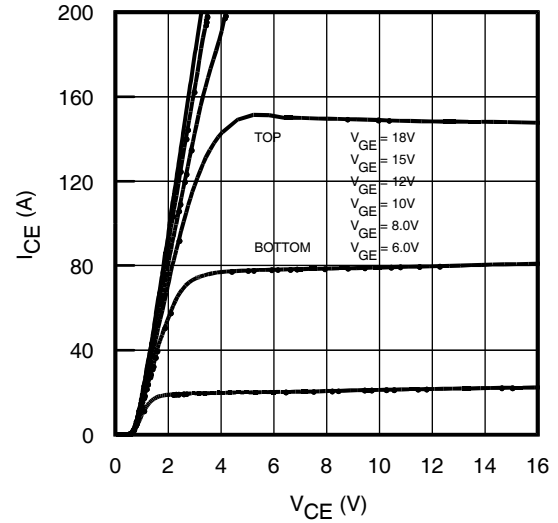


Fig 2. Typical Output Characteristics @ 75°C

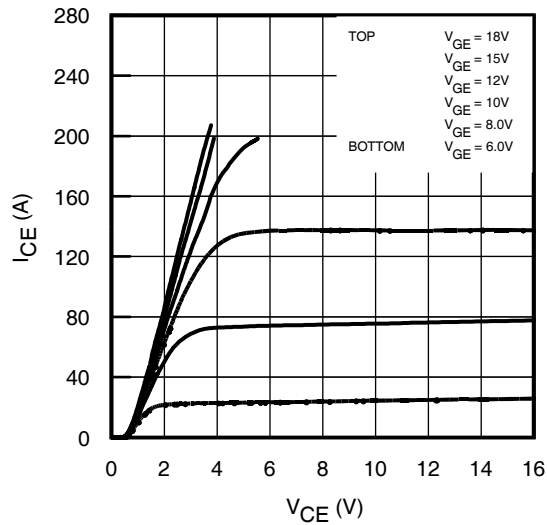


Fig 3. Typical Output Characteristics @ 125°C

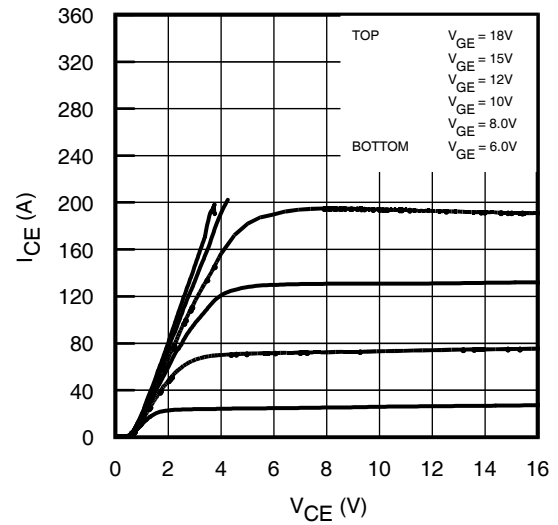


Fig 4. Typical Output Characteristics @ 150°C

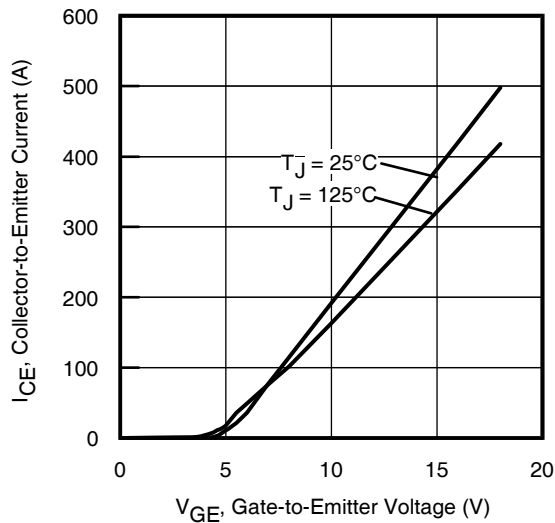


Fig 5. Typical Transfer Characteristics

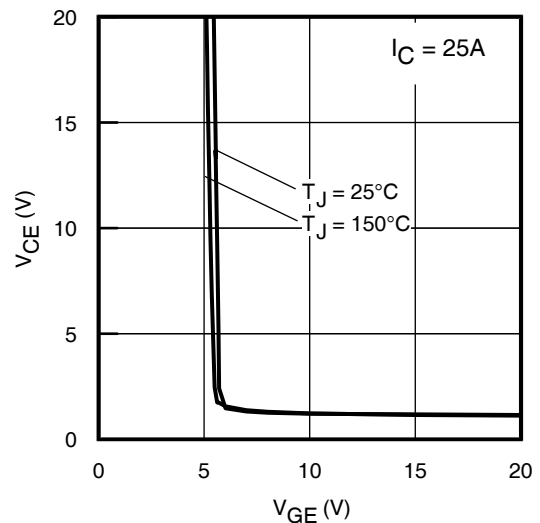


Fig 6. $V_{CE(ON)}$ vs. Gate Voltage

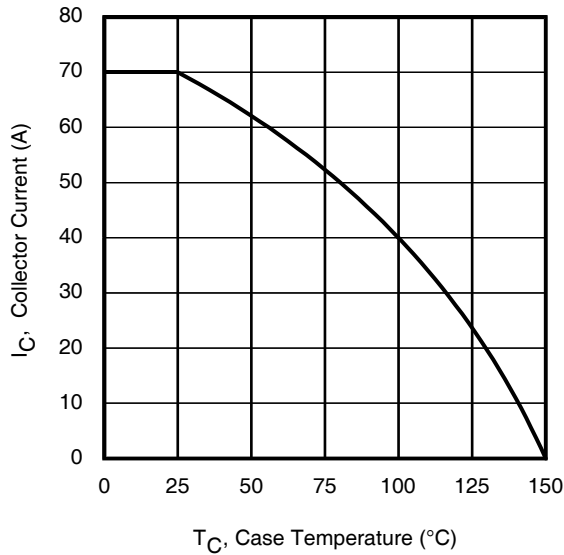


Fig 7. Maximum Collector Current vs. Case Temperature

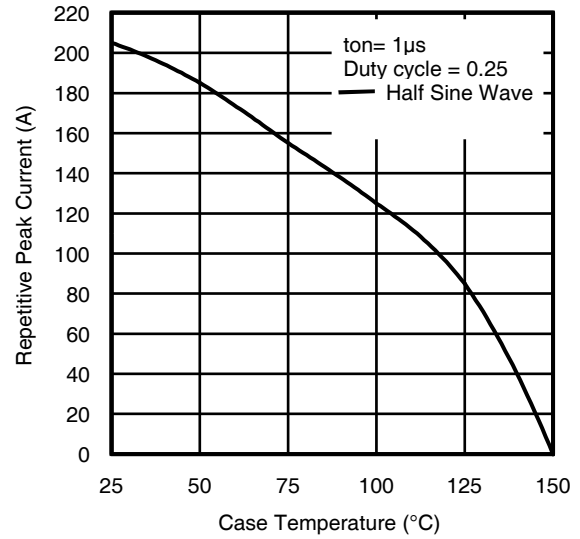


Fig 8. Typical Repetitive Peak Current vs. Case Temperature

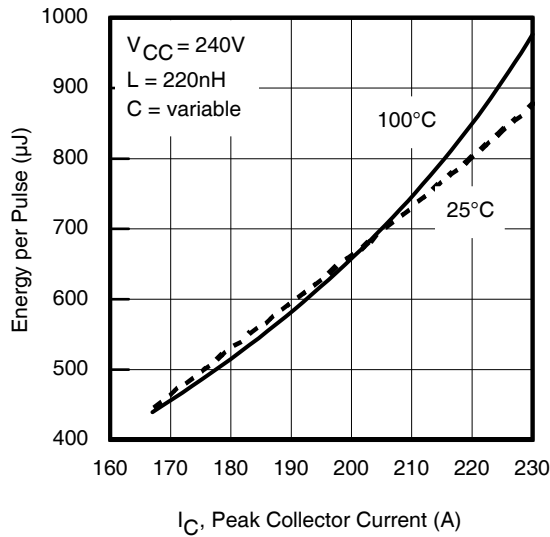


Fig 9. Typical E_{PULSE} vs. Collector Current

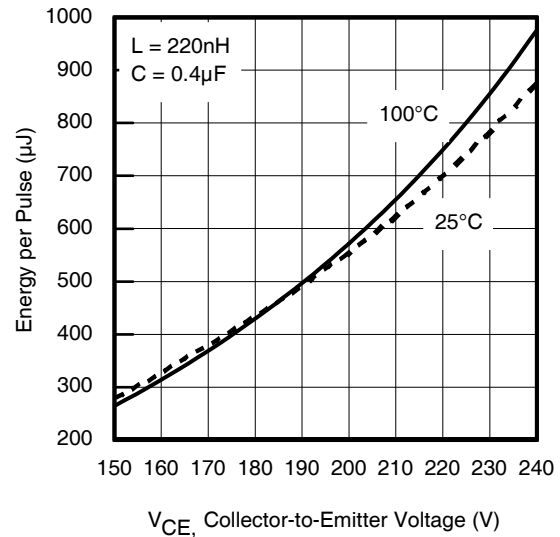


Fig 10. Typical E_{PULSE} vs. Collector-to-Emitter Voltage

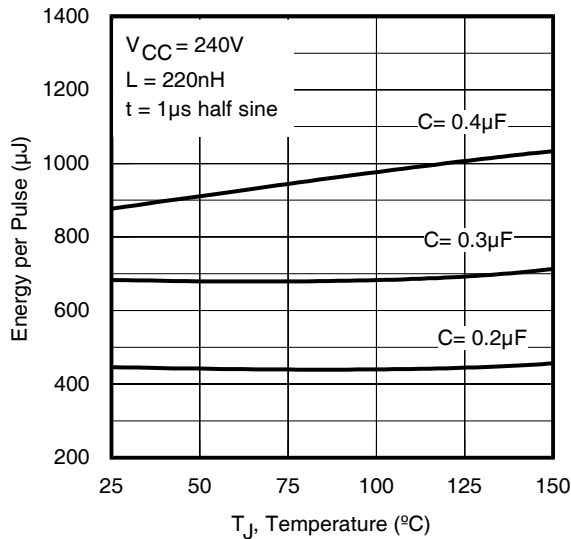


Fig 11. E_{PULSE} vs. Temperature

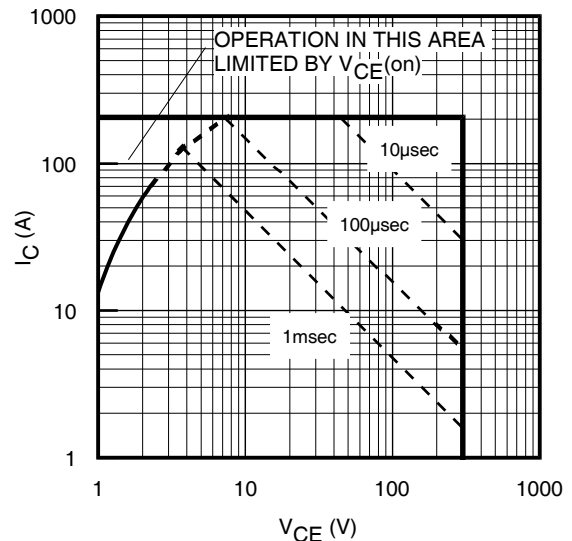


Fig 12. Forward Bias Safe Operating Area

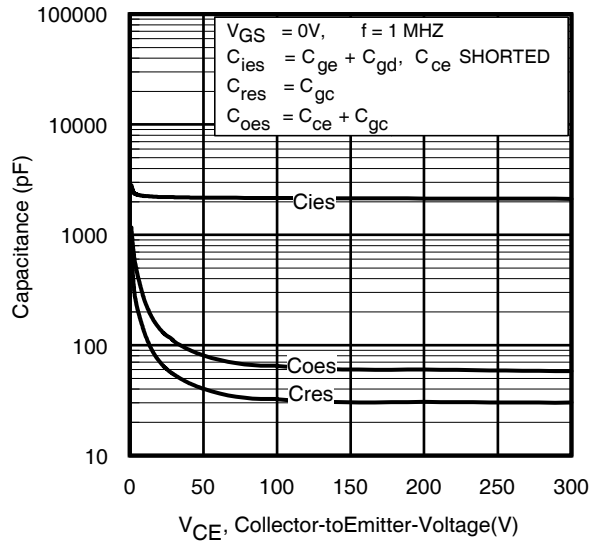


Fig 13. Typical Capacitance vs. Collector-to-Emitter Voltage

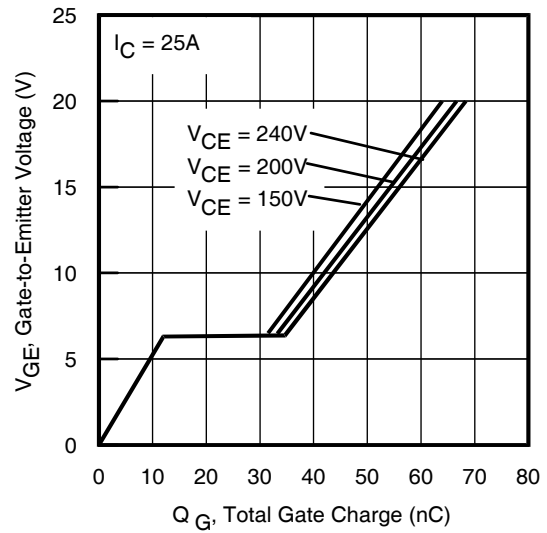


Fig 14. Typical Gate Charge vs. Gate-to-Emitter Voltage

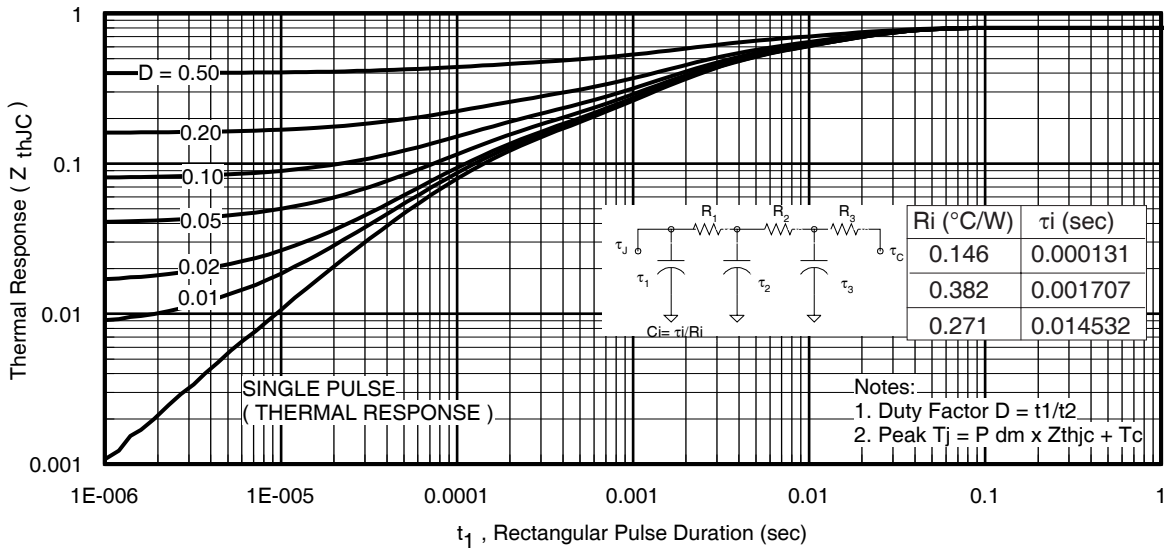


Fig 15. Maximum Effective Transient Thermal Impedance, Junction-to-Case

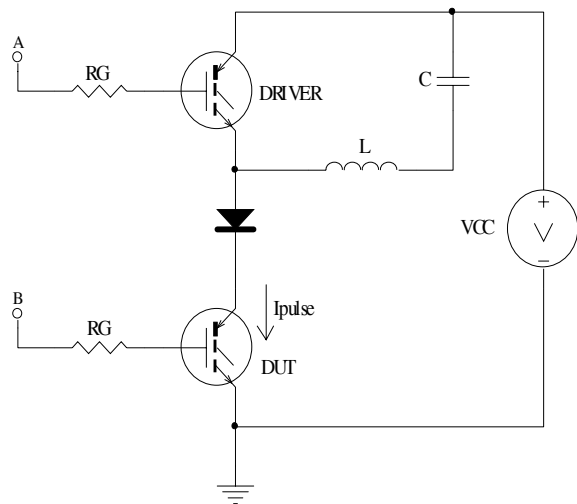


Fig 16a. t_{st} and E_{PULSE} Test Circuit

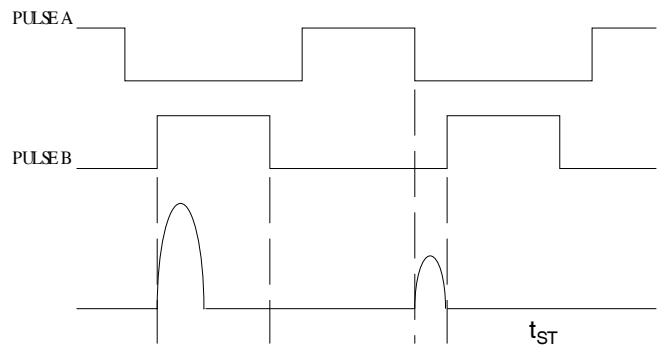


Fig 16b. t_{st} Test Waveforms

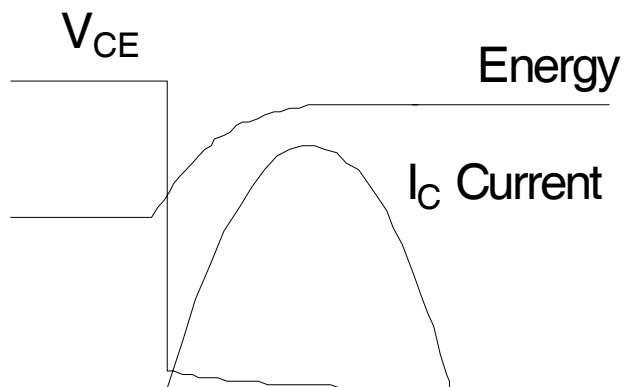


Fig 16c. E_{PULSE} Test Waveforms

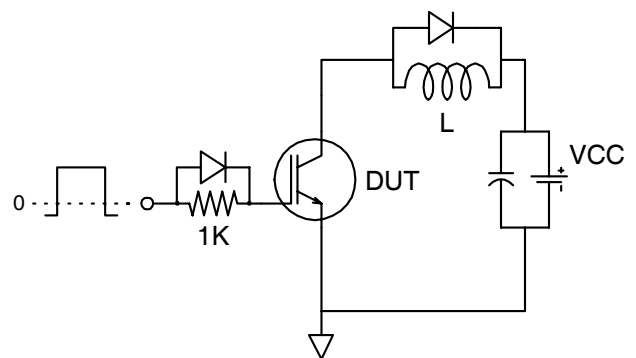
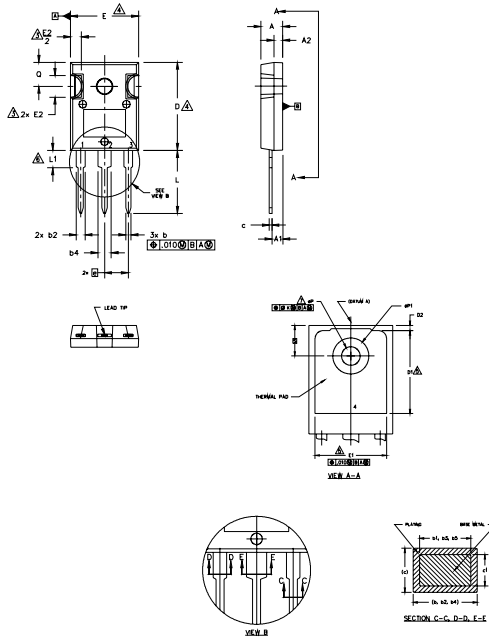


Fig. 17 - Gate Charge Circuit (turn-off)

TO-247AC Package Outline Dimensions are shown in millimeters (inches)



- NOTES:
1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
 2. DIMENSIONS ARE SHOWN IN INCHES.
 3. CONTOUR OF SLOT OPTIONAL.
 4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
 6. LEAD FINISH UNCONTROLLED IN L1.
 7. #P TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
 8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC.

| SYMBOL | DIMENSIONS | | | | NOTES |
|--------|------------|------|-------------|-------|-------|
| | INCHES | | MILLIMETERS | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | .183 | .209 | 4.65 | 5.31 | |
| A1 | .087 | .102 | 2.21 | 2.59 | |
| A2 | .059 | .098 | 1.50 | 2.49 | |
| b | .039 | .065 | 0.99 | 1.40 | |
| b1 | .039 | .053 | 0.99 | 1.35 | |
| b2 | .065 | .094 | 1.65 | 2.39 | |
| b3 | .065 | .092 | 1.65 | 2.34 | |
| b4 | .102 | .135 | 2.59 | 3.43 | |
| b5 | .102 | .133 | 2.59 | 3.38 | |
| c | .015 | .035 | 0.38 | 0.89 | |
| c1 | .015 | .033 | 0.38 | 0.84 | |
| D | .776 | .815 | 19.71 | 20.70 | 4 |
| D1 | .515 | - | 13.08 | - | 5 |
| D2 | .020 | .053 | 0.51 | 1.35 | |
| E | .602 | .625 | 15.29 | 15.87 | 4 |
| E1 | .530 | - | 13.46 | - | |
| E2 | .178 | .216 | 4.52 | 5.49 | |
| e | .215 BSC | | 5.46 BSC | | |
| e1 | .010 | | 0.25 | | |
| L | .559 | .634 | 14.20 | 16.10 | |
| L1 | .146 | .169 | 3.71 | 4.29 | |
| L2 | .140 | .144 | 3.56 | 3.66 | |
| #P | - | .291 | - | 7.39 | |
| Q | .209 | .224 | 5.31 | 5.69 | |
| S | .217 BSC | | 5.51 BSC | | |

LEAD ASSIGNMENTS

- HEXLET**
- 1.- GATE
 - 2.- DRAIN
 - 3.- SOURCE
 - 4.- DRAIN

IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

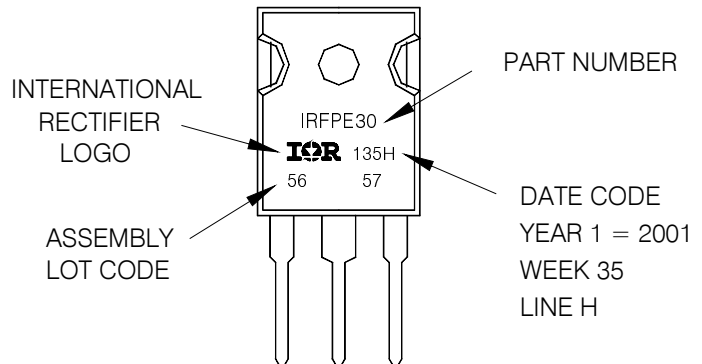
DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30
 WITH ASSEMBLY
 LOT CODE 5657
 ASSEMBLED ON WW 35, 2001
 IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position
 indicates "Lead-Free"



TO-247AC package is not recommended for Surface Mount Application.

The specifications set forth in this data sheet are the sole and exclusive specifications applicable to the identified product, and no specifications or features are implied whether by industry custom, sampling or otherwise. We qualify our products in accordance with our internal practices and procedures, which by their nature do not include qualification to all possible or even all widely used applications. Without limitation, we have not qualified our product for medical use or applications involving hi-reliability applications. Customers are encouraged to and responsible for qualifying product to their own use and their own application environments, especially where particular features are critical to operational performance or safety. Please contact your IR representative if you have specific design or use requirements or for further information.

Data and specifications subject to change without notice. This product has been designed for the Industrial market. Qualification Standards can be found on IR's Web site.

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>